SMTT850D-2*50

High Performance Infrared TOP LED

This consists of two large AlGaAs LEDs mounted on the lead frame as TOP LED package with copper heat sink. It is 42mW typical of output power and 20mW/sr of radiant intensity. This is suitable for strobe flash light and able to emit 0.8W/sr light operating at pulsed current 4A under 3.5V type. It emits a spectral band of radiation at 850nm.

<Specifications>

- 1. Product Name: TOP IR LED
- 2. Type Number: SMT850D-2*50
- 3. Chip:
- Chip Material: AlGaAs
- Dimension: 500um x 500um
- Number: 2pcs
- Peak Wavelength: 850nm

4.Package

- Lead Frame Die: Silver Plated
- Package Resin: PPA Resin
- Cap: Clear Epoxy Resin
- Heatsink: Copper

Outer Dimension (Unit:mm)



Absolute Maximum Ratings[Ta=25°C]							
Item	Symbol	Maximum Rated Value	Unit				
Power Dissipation	PD	300	mW				
Forward Current	IF	200	mA				
Pulse Forward Current*	IFP	4000	mA				
Reverse Voltage	VR	5	V				
Operating Temperature	TOPR	-20 ~ +80	°C				
Storage Temperature	TSTG	-30 ~ +80	°C				
Soldering Temperature**	TSOL	255	°C				

* Duty=1% and Pulse width=10µs

** Soldering condition must be completed within 10 second at 255°C.

Electro-Optical Characteristics [Ta=25°C]									
Item	Symbol	Condition	Minimum	Typical	Maximum	Unit			
Forward Voltage	VF	IF=100mA DC		1.45	1.60	V			
		IFP=4A		3.5	4.2				
Reverse Current	IR	VR=5V			10	uA			
Total Radiated Power*	PO	IF=100mA DC	32	42		mW			
Radiant Intensity**	IE	IF=100mA DC		20		mW/sr			
		IFP=4A		800					
Peak wavelength	λΡ	IF=50mA DC	835	850	865	nm			
Half Width	Δλ	IF=50mA DC		28		nm			
Viewing Half Angle	θ1/2	IF=50mA DC		±60		deg			
Rise Time	Tr	IF=50mA DC		15		ns			
Fall Time	tf	IF=50mA DC		10		ns			

* Measured by Photodyne #500

** Measured by Tektronix J-6512

- Heat sink should be provided by soldering for stable use.

